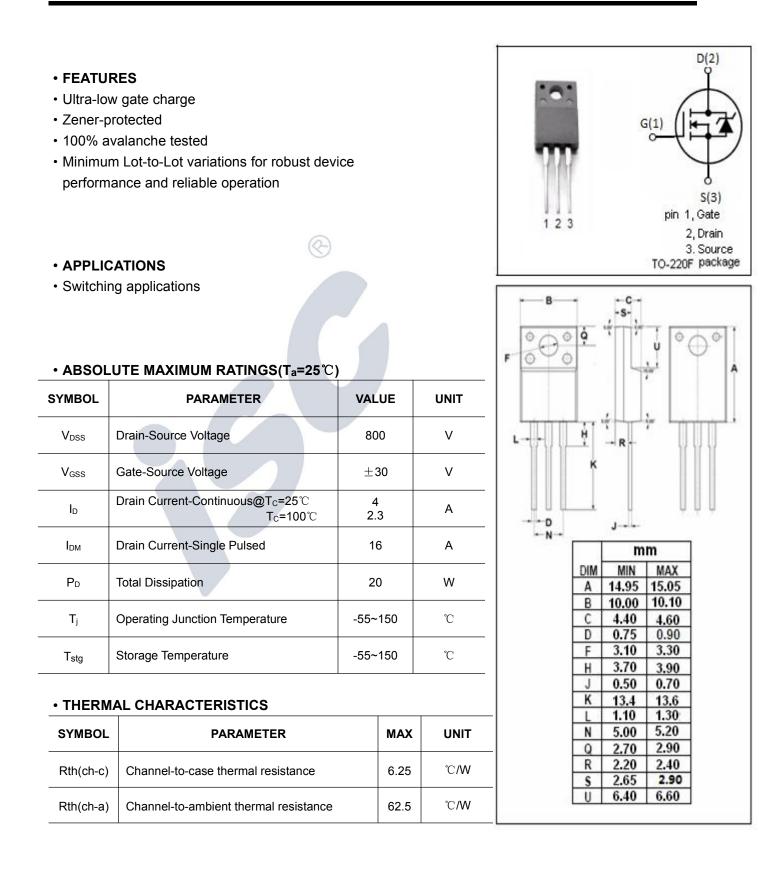


#### INCHANGE SEMICONDUCTOR

#### **Isc N-Channel MOSFET Transistor**

## STF5N80K5



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# **Isc N-Channel MOSFET Transistor**

# STF5N80K5

#### **ELECTRICAL CHARACTERISTICS**

#### $T_{C}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> = 1mA	800			V
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> =±30V; I <sub>D</sub> =0.1mA	3		5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =2A		1.50	1.75	Ω
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0V			±10	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = 800V; V <sub>GS</sub> = 0V; TJ=25℃ TJ=125℃			1 50	μ Α
V <sub>SDF</sub>	Diode forward voltage	I <sub>SD</sub> =4A, V <sub>GS</sub> = 0 V			1.6	v



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